

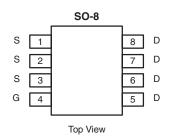
P-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^b	Q _g (Typ.)			
	0.009 at $V_{GS} = -4.5 \text{ V}$	- 13.7				
- 8	0.011 at V _{GS} = - 2.5 V	- 12.4	55 nC			
	0.016 at V _{GS} = - 1.8 V	- 10				

FEATURES

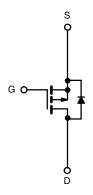
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- 1.8 V Rated
- 100 % R_g Tested





Ordering Information: Si4465ADY-T1-E3 (Lead (Pb)-free)

Si4465ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	$T_A = 25$ °C, unles	ss otherwise n	oted	
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	- 8	V	
Gate-Source Voltage	V_{GS}	± 8	V	
	T _A = 25 °C		- 13.7	
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 70 °C	1	- 11	
Continuous Drain Current (1 _J = 150 °C) ⁻⁵	T _C = 25 °C	- I _D	- 20	A
	T _C = 70 °C		- 16	
Pulsed Drain Current	I _{DM}	- 40	İ	
Continuous Source Current (Diode Conduction) ^{a, b}		I _S	- 2.5	
		I _{SM}	40	
	T _A = 25 °C		3.0	
Mariana Barra Birata da h	T _A = 70 °C	P _D	1.95	W
Maximum Power Dissipation ^{a, b}	T _C = 25 °C		6.5	VV
	T _C = 70 °C		4.2	
Operating Junction and Storage Temperature Ran	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manifestory Investigation to Ambient (MOCEFT)	t ≤ 10 s	R _{thJA}	34	41	°C/W	
Maximum Junction-to-Ambient (MOSFET) ^a	Steady State		67	80		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	15	19		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. $t \le 10 \text{ s}$.

Si4465ADY

Vishay Siliconix



SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static				•		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.45		- 1.0	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA
Zara Cata Valtaga Drain Current	lass	V _{DS} = - 8 V, V _{GS} = 0 V			- 1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -8 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 5	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α
		$V_{GS} = -4.5 \text{ V}, I_D = -14 \text{ A}$		0.0075	0.009	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -12 \text{ A}$		0.0092	0.011	Ω
		$V_{GS} = 1.8 \text{ V}, I_D = 10 \text{ A}$		0.013	0.016	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 14 A		58		S
Diode Forward Voltage ^a	V_{SD}	I _S = - 2.1 A, V _{GS} = 0 V		- 0.57	- 1.2	V
Dynamic ^b			'	•		l
Total Gate Charge	Q_g			55	85	
Gate-Source Charge	Q_{gs}	$V_{DS} = -4 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -14 \text{ A}$		6		nC
Gate-Drain Charge	Q_{gd}			10		
Gate Resistance	R_{g}			2.5	3.8	Ω
Turn-On Delay Time	t _{d(on)}			33	50	
Rise Time	t _r	V_{DD} = - 4 V, R_L = 4 Ω		170	255	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong10~\text{A},~\text{V}_\text{GEN}=4.5~\text{V},~\text{R}_\text{g}=\text{6}~\Omega$		168	255	ns
Fall Time	t _f			112	170	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.1 A, dl/dt = 100 A/μs		85	130	
Body Diode Reverse Recovery Charge	Q _{rr}	1 ₁ = - 2.1 Λ, απαι = 100 Λ/μδ		81	125	nC

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

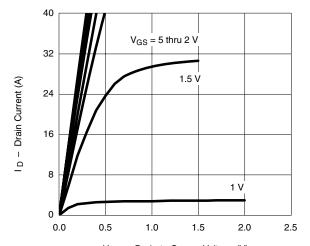
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.



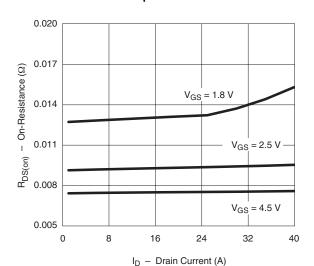


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

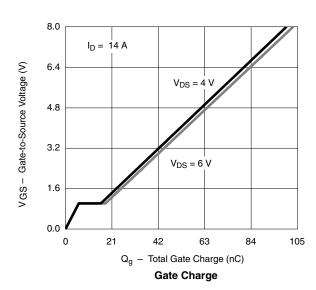


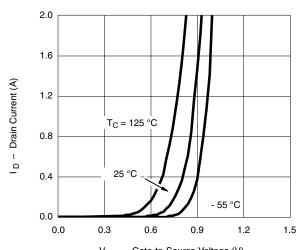
V_{DS} - Drain-to-Source Voltage (V)

Output Characteristics



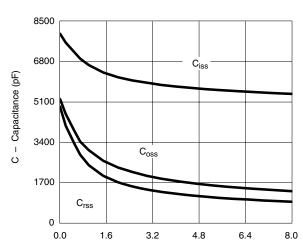
On-Resistance vs. Drain Current





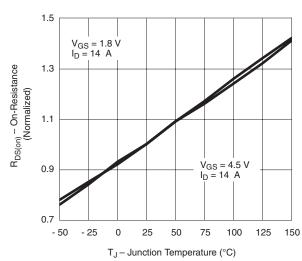
V_{GS} - Gate-to-Source Voltage (V)





 $V_{DS}\,-\,$ Drain-to-Source Voltage (V)

Capacitance

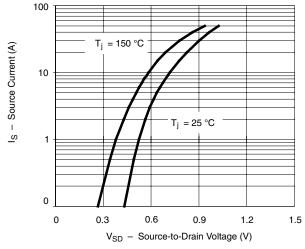


On-Resistance vs. Junction Temperature

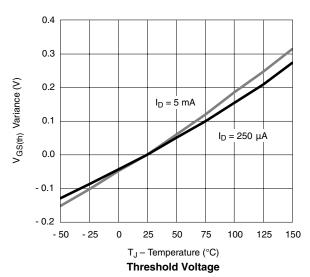
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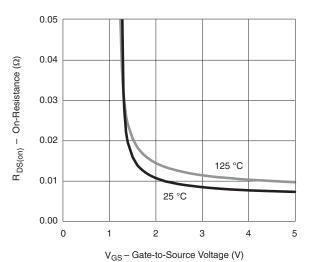
VISHAY

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

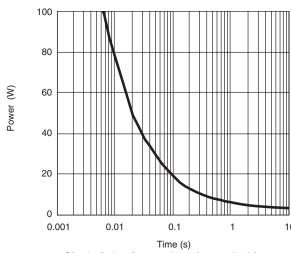


Source-Drain Diode Forward Voltage

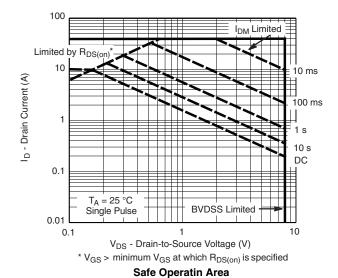




On-Resistance vs. Gate-to-Source Voltage

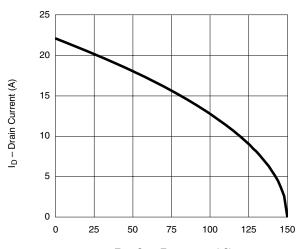


Single Pulse Power, Junction-to-Ambient



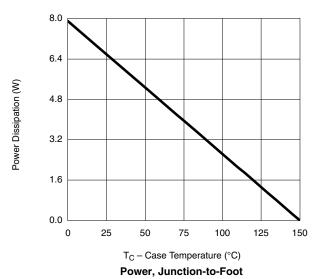


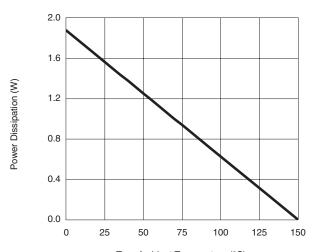
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



T_C - Case Temperature (°C)

Current Derating





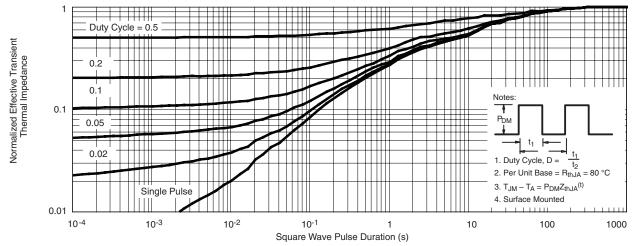
T_A – Ambient Temperature (°C) **Power, Junction-to-Ambient**

^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

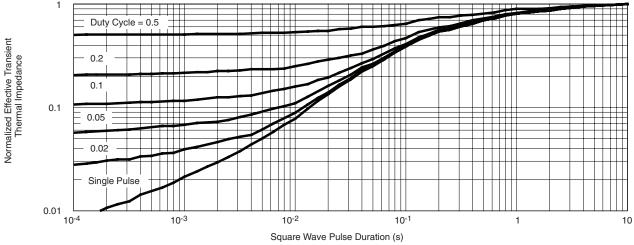
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INCHES		
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I. 11-Sep-06					

DWG: 5498

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LON NOTE



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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